

Silicon NPN Power Transistors

S2055

DESCRIPTION

www.datasheet4u.com

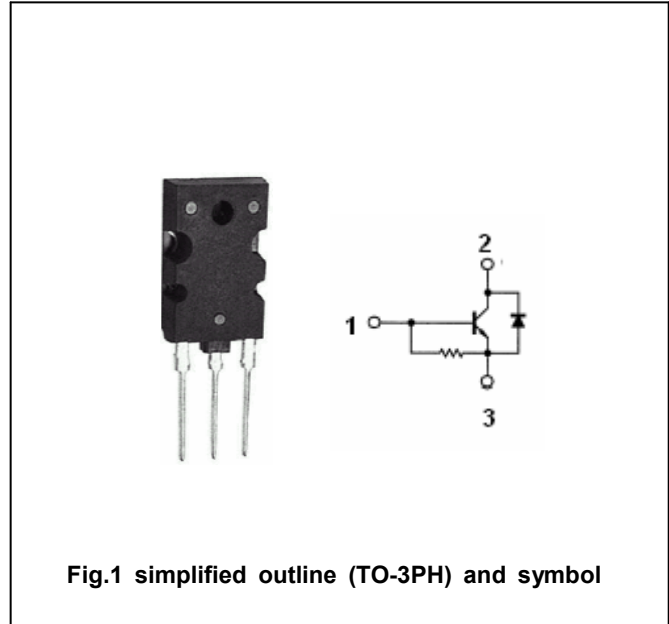
- With TO-3PH package
- High voltage ,high speed
- Low collector saturation voltage
- Built-in damper diode

APPLICATIONS

- Color TV horizontal output applications
- Color TV switching regulator applications

PINNING □ See Fig.2 □

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

ABSOLUTE MAXIMUM RATINGS ($T_C=25^\circ$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	1500	V
V_{CEO}	Collector-emitter voltage	Open base	700	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		8	A
I_{CM}	Collector current-peak		15	A
I_B	Base current		4	A
P_C	Collector power dissipation	$T_C=25^\circ$	125	W
T_j	Junction temperature		150	□
T_{stg}	Storage temperature		-55~150	□

Silicon NPN Power Transistors

S2055

CHARACTERISTICS

T_j=25°C unless otherwise specified

www.datasheet4u.com

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEQ(SUS)}	Collector-emitter sustaining voltage	I _B =500mA ; V _{BE} =-1.7V; L=40mH	700			V
V _{CE(sat)}	Collector-emitter saturation voltage	I _C =4.5A ; I _B =1.0A			5.0	V
V _{BE(sat)}	Base-emitter saturation voltage	I _C =4.5A ; I _B =1.0A			1.2	V
I _{CBO}	Collector cut-off current	V _{CB} =1500V; V _{BE} =0			1.0	mA
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			300	mA
h _{FE-1}	DC current gain	I _C =1A ; V _{CE} =5V	10		30	
h _{FE-2}	DC current gain	I _C =4.5A ; V _{CE} =5V	4.5		9	
C _{OB}	Collector output capacitance	I _E =0 ; V _{CB} =10V; f=1MHz		95		pF
f _T	Transition frequency	I _C =0.1A ; V _{CE} =10V		2		MHz

PACKAGE OUTLINE

www.datasheet4u.com

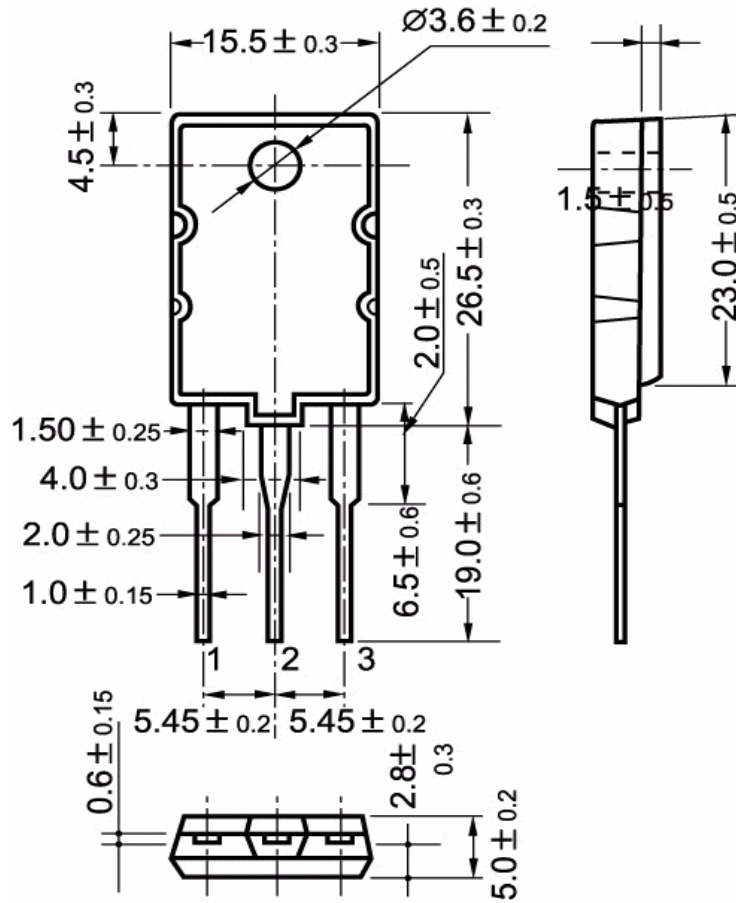


Fig.2 outline dimensions